

isc Silicon NPN Power Transistor
2SC1971
DESCRIPTION

- High Power Gain-
: $G_{pe} \geq 7\text{dB}$, $P_O = 6\text{W}$; $V_{CE} = 13.5\text{V}$
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

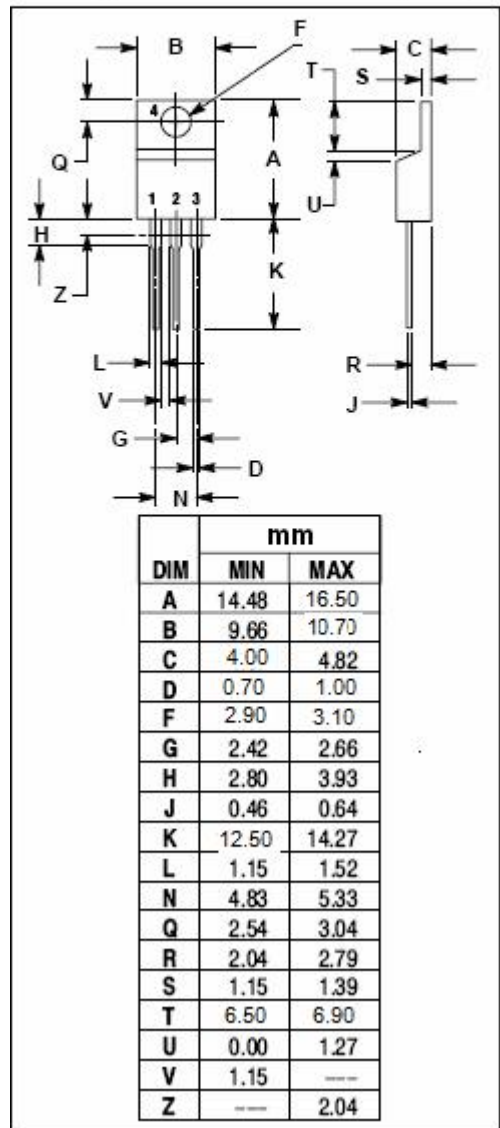
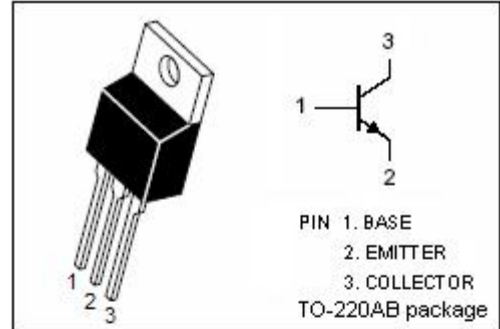
- Designed for RF power amplifiers on VHF band mobile radio applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--------------------------------------------------------|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 35 | V |
| V_{CEO} | Collector-Emitter Voltage $R_{BE} = \infty$ | 17 | V |
| V_{EBO} | Emitter-Base Voltage | 4 | V |
| I_C | Collector Current | 2 | A |
| P_C | Collector Power Dissipation @ $T_C = 25^\circ\text{C}$ | 12.5 | W |
| | Collector Power Dissipation @ $T_a = 25^\circ\text{C}$ | 1.5 | |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|-----------------------------------------|-----|---------------------------|
| $R_{th\ j-a}$ | Thermal Resistance, Junction to Ambient | 83 | $^\circ\text{C}/\text{W}$ |
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 10 | $^\circ\text{C}/\text{W}$ |



isc Silicon NPN Power Transistor**2SC1971****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------|-------------------------------------|---------------------------------------------------------------------|-----|------|-----|------|
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C=10\text{mA}$, $I_E=0$ | 35 | | | V |
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C=50\text{mA}$; $R_{BE}=\infty$ | 17 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E=5\text{mA}$, $I_C=0$ | 4 | | | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB}=25\text{V}$; $I_E=0$ | | | 0.5 | mA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB}=3\text{V}$; $I_C=0$ | | | 0.5 | mA |
| h_{FE} | DC Current Gain | $I_C=0.1\text{A}$; $V_{CE}=10\text{V}$ | 10 | | 180 | |
| P_O | Output Power | $V_{CC}=13.5\text{V}$; $P_{in}=0.6\text{W}$; $f=175\text{MHz}$ | 6 | | | W |
| η_C | Collector Efficiency | | 7 | | | DB |
| C_{OB} | Output Capacitance | $I_E=0$; $V_{CB}=20\text{V}$, $f_{test}=1\text{MHz}$ | | | 18 | pF |

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